

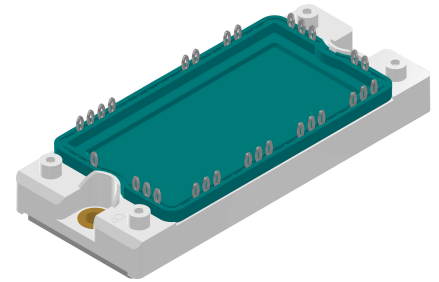
High Voltage Standard Rectifier Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 2200 \text{ V}$	$V_{CES} = 1700 \text{ V}$
$I_{DAV} = 210 \text{ A}$	$I_{C25} = 145 \text{ A}$
$I_{FSM} = 1000 \text{ A}$	$V_{CE(sat)} = 1.8 \text{ V}$

3~ Rectifier Bridge + Brake Unit + NTC

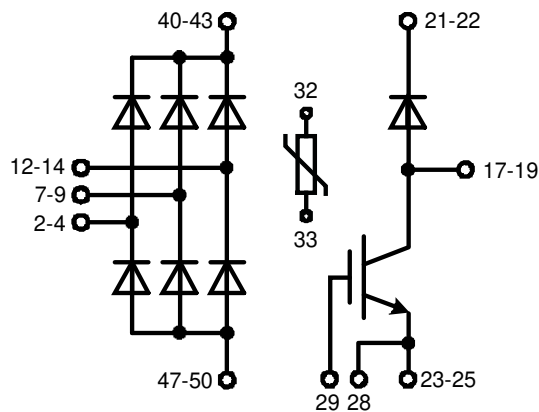
Part number

MDNA210UB2200PTED



Backside: isolated

 E72873



Features / Advantages:

- Brake with Infineon IGBT³

Applications:

- 3~ Rectifier with brake unit for drive inverters

Package: E2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		2300	V
V_{RRM}	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		2200	V
I_R	reverse current	$V_R = 2200$ V		$T_{VJ} = 25^{\circ}C$		100	μA
		$V_R = 2200$ V		$T_{VJ} = 150^{\circ}C$		2	mA
V_F	forward voltage drop	$I_F = 70$ A		$T_{VJ} = 25^{\circ}C$		1.23	V
		$I_F = 210$ A				1.75	V
		$I_F = 70$ A		$T_{VJ} = 125^{\circ}C$		1.19	V
		$I_F = 210$ A				1.67	V
I_{DAV}	bridge output current	$T_C = 85^{\circ}C$		$T_{VJ} = 150^{\circ}C$		210	A
		rectangular	$d = \frac{1}{3}$				
V_{FO}	threshold voltage			$T_{VJ} = 150^{\circ}C$		0.82	V
r_F	slope resistance					5.2	m Ω
						} for power loss calculation only	
R_{thJC}	thermal resistance junction to case					0.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.1		K/W
P_{tot}	total power dissipation			$T_C = 25^{\circ}C$		250	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		1.00	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.08	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		850	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		920	A
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		5.00	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		4.85	kA ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		3.62	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		3.52	kA ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^{\circ}C$		33	pF



Brake IGBT + Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}C$			1700	V	
V_{GES}	max. DC gate voltage				± 20	V	
V_{GEM}	max. transient gate emitter voltage				± 30	V	
I_{C25}	collector current	$T_C = 25^{\circ}C$			145	A	
I_{C80}		$T_C = 80^{\circ}C$			100	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}C$			540	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 75\text{ A}; V_{GE} = 15\text{ V}$		1.8	2.16	V	
				2.1		V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4\text{ mA}; V_{GE} = V_{CE}$	5.2	5.8	6.4	V	
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.1	mA	
				0.7		mA	
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 900\text{ V}; V_{GE} = 15\text{ V}; I_C = 75\text{ A}$		1200		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 900\text{ V}; I_C = 75\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 3.9\ \Omega$	$T_{VJ} = 125^{\circ}C$		320	ns	
t_r	current rise time				50	ns	
$t_{d(off)}$	turn-off delay time				550	ns	
t_f	current fall time				400	ns	
E_{on}	turn-on energy per pulse				15	mJ	
E_{off}	turn-off energy per pulse				18	mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 3.9\ \Omega$					
I_{CM}		$V_{CEK} = 1700\text{ V}$			200	A	
SCSOA	short circuit safe operating area	$V_{CEK} = 1700\text{ V}$					
t_{SC}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15$	$T_{VJ} = 125^{\circ}C$		10	μs	
I_{SC}	short circuit current	$R_G = 3.9\ \Omega$; non-repetitive		400		A	
R_{thJC}	thermal resistance junction to case				0.23	K/W	
R_{thCH}	thermal resistance case to heatsink				0.08	K/W	
Brake Diode							
V_{RRM}	max. repetitive reverse voltage				1700	V	
I_{F25}	forward current		$T_C = 25^{\circ}C$		81	A	
I_{F80}			$T_C = 80^{\circ}C$		54	A	
V_F	forward voltage	$I_F = 60\text{ A}$	$T_{VJ} = 25^{\circ}C$		2.20	V	
			$T_{VJ} = 125^{\circ}C$	2.00		V	
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}C$		0.1	mA	
			$T_{VJ} = 125^{\circ}C$		1.2	mA	
Q_{rr}	reverse recovery charge	$V_R = 900\text{ V}$ $-di_f/dt = 1600\text{ A}/\mu s$ $I_F = 60\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}C$		15	μC	
I_{RM}	max. reverse recovery current				100	A	
t_{rr}	reverse recovery time				550	ns	
E_{rec}	reverse recovery energy				6.5	mJ	
R_{thJC}	thermal resistance junction to case				0.6	K/W	
R_{thCH}	thermal resistance case to heatsink				0.2	K/W	

Package E2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			30	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				176		g
M_D	mounting torque		3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute	3600 3000			V V
		50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA				


Part description

M = Module
 D = Diode
 N = High Voltage Standard Rectifier
 A = (>= 2000V)
 210 = Current Rating [A]
 UB = 3- Rectifier Bridge + Brake Unit
 2200 = Reverse Voltage [V]
 PT = PressFit-Pin, Thermistor
 ED = E2-Pack
 - = Hyphen
 PC = Phase Change Material

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDNA210UB2200PTED	MDNA210UB2200PTED	Blister	28	515668
Alternative	MDNA210UB2200PTED-PC	MDNA210UB2200PTED	Blister	28	515430

Temperature Sensor NTC

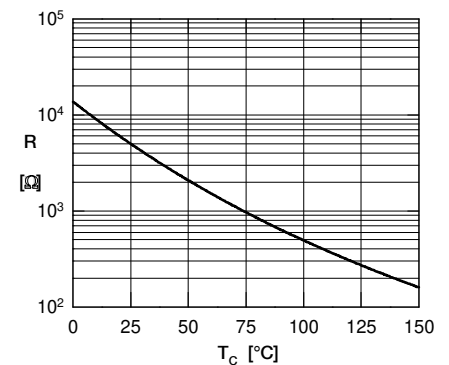
Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4.85	5	5.15	k Ω
$B_{25/50}$	temperature coefficient			3375		K

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^\circ\text{C}$

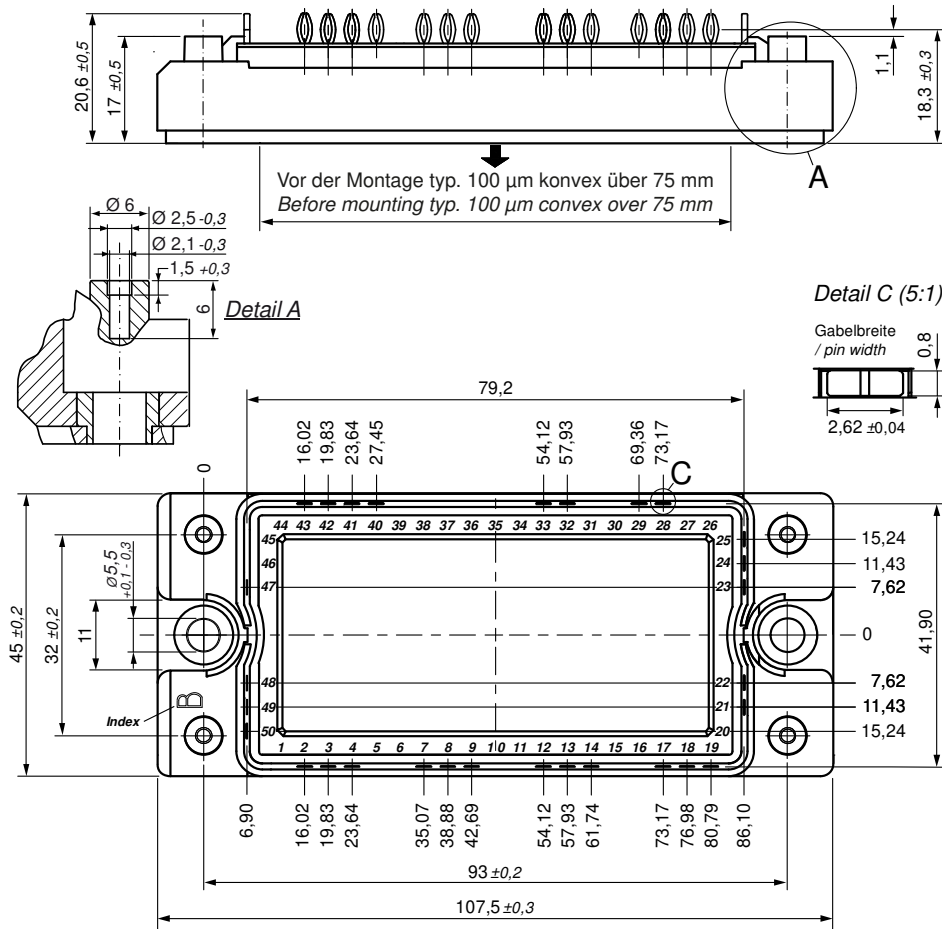
		Rectifier	Brake IGBT +	Brake Diode	
V_0	threshold voltage	0.82	1.1	1.22	V
R_0	slope resistance *	3.1	17.9	13	m Ω



Typ. NTC resistance vs. temperature



Outlines E2-Pack

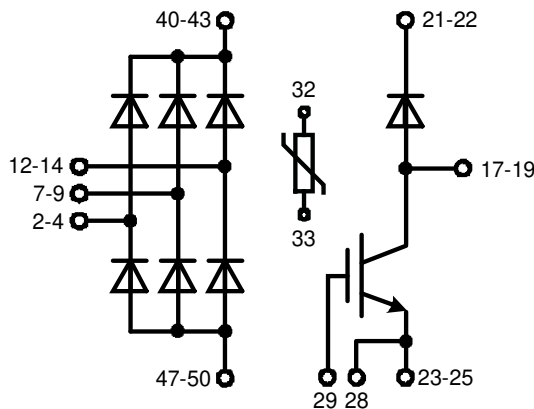


Bemerkung / Note:

- Nicht tolerierte Maße nach / Measure without tolerances according DIN ISO 2768-T1-m
- PCB-Lochmuster / PCB hole pattern: **see pin position**
- Toleranz Pin-Position und PCB-Lochmuster / Tolerance of pin position and PCB hole pattern: $\oplus 0.1$
- Bohrlochdurchmesser / Diameter of drill: **Ø 2.35 mm**
- Endlochdurchmesser / Diameter of plated holes: **Ø 2.14 - 2.29 mm** (Cu thickness in via typ. 50 µm)
- Beschichtung / Plating: **chem. Sn max. 15 µm**
- Einpresskraft / Insert Force: per terminal with a typ. insert speed of 7 mm/s: **typ. 90 N**
- Weitere Angaben / Further information: www.ixys.com **Application note IXAN0077**
- Montageanleitung / Mounting instruction: www.ixys.com **Application note IXAN0024**

Detail A: PCB-Montage / Mounting on PCB^L

- Empfohlene, selbstschneidende Schraube / Recommended, self-tapping screw: **EJOT PT®** (Größe / size: **K25**)^L
- Max. Schraubenlänge / Max. screw length: **PCB-Dicke / thickness + 6 mm** (max. Lochtiefe / hole depth)^L
- Empfohlenes Drehmoment / Recommended mounting torque: **1.5 Nm**



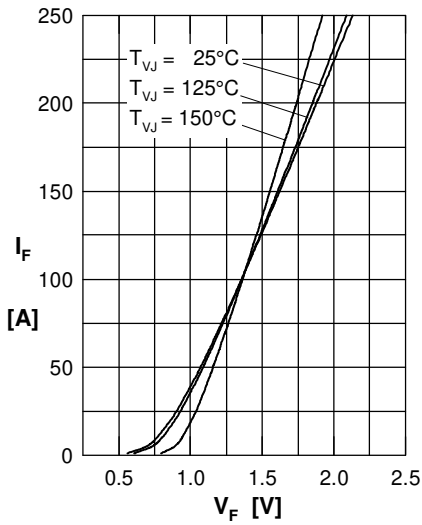
Rectifier


Fig. 1 Forward current versus voltage drop per diode

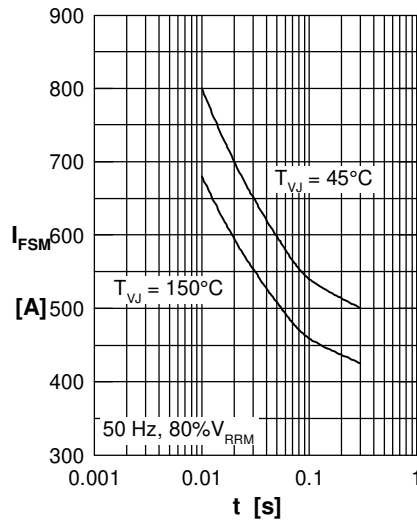


Fig. 2 Surge overload current vs. time per diode

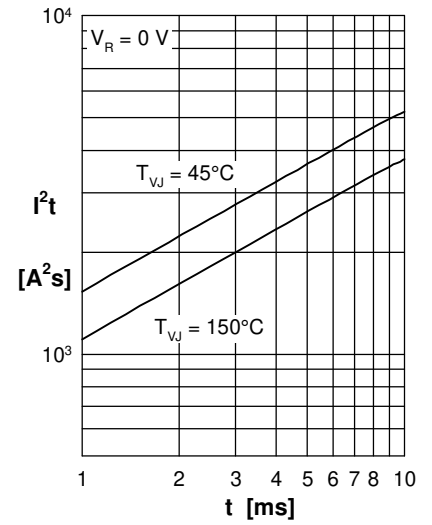
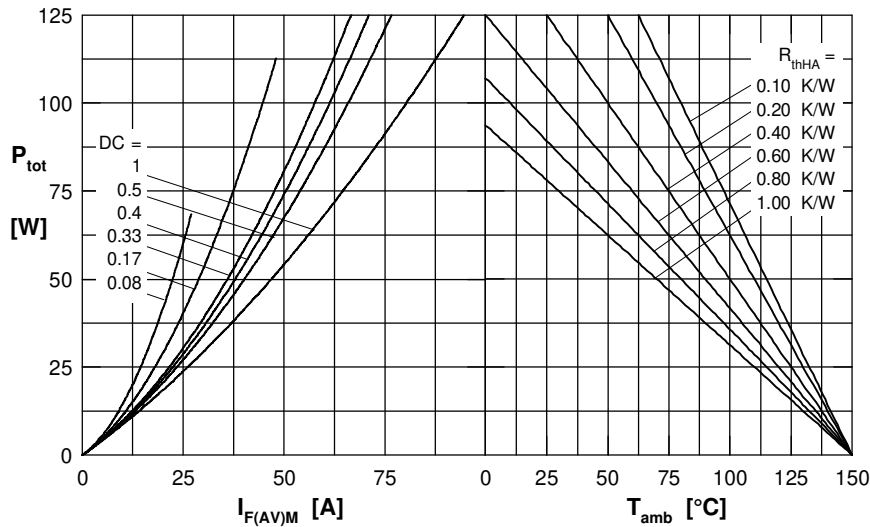

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

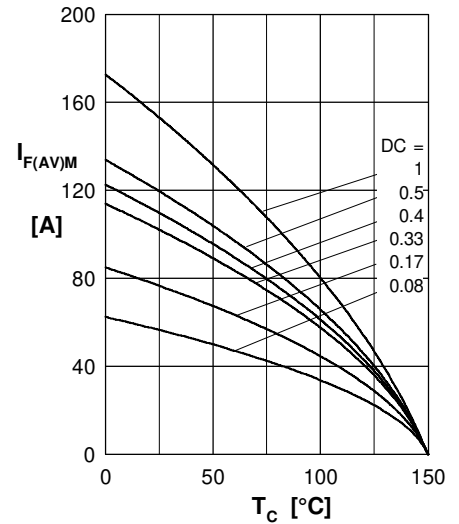


Fig. 5 Max. forward current vs. case temperature per diode

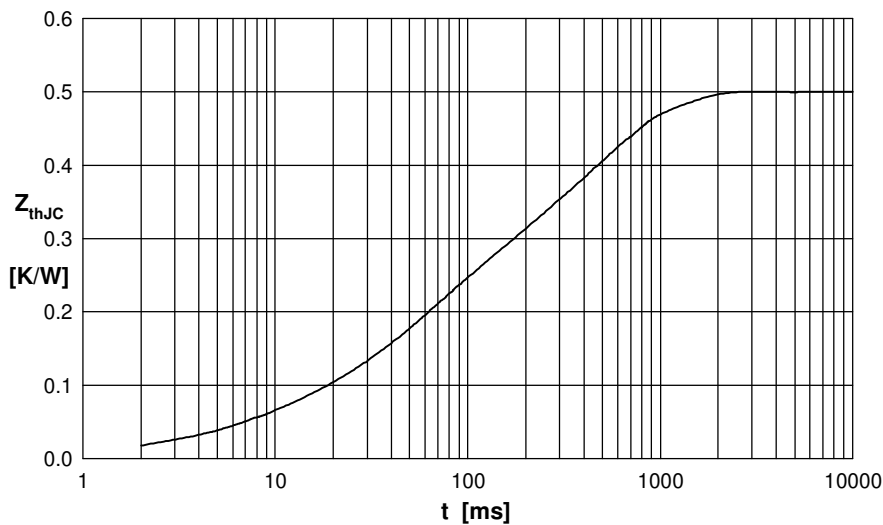


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.030	0.006
2	0.003	0.007
3	0.182	0.045
4	0.285	0.450